ADE–208–438 E (Z)

HAT2016R

Silicon N Channel Power MOS FET

HITACHI

6th. Edition
Jan. 1996

Application

High speed power switching

Features

- Low on–resistance
- Capable of 4V gate drive
- Low drive current
- High density mounting

Ordering Information

Hitachi Cord	FP–8DA
EIAJ Cord	—
JEDEC Cord	MS–012AA

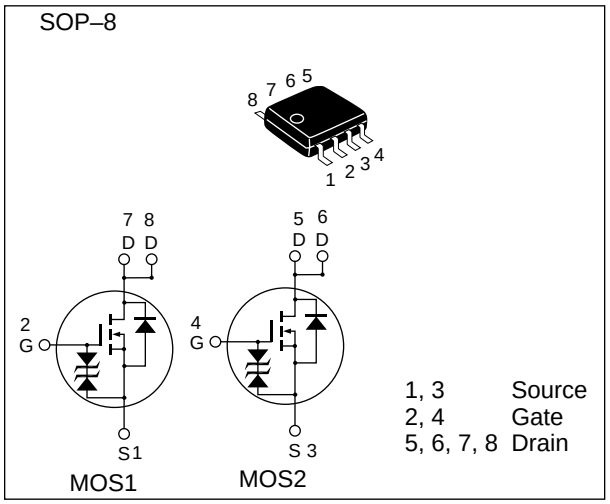

Table 1 Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	V_{DSS}	30	V
Gate to source voltage	V_{GSS}	±20	V
Drain current	I_D	6.5	A
Drain peak current	$I_{D(pulse)}$*	52	A
Channel dissipation	Pch***	3	W
Channel dissipation	Pch**	2	W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	–55 to +150	°C

* PW ≤ 10 µs, duty cycle ≤ 1 %
** 1 Drive operation : When using the glass epoxy board (FR4 40 x 40x 1.6 mm), PW ≤ 10 s
*** 2 Drive operation : When using the glass epoxy board (FR4 40 x 40x 1.6 mm), PW ≤ 10 s

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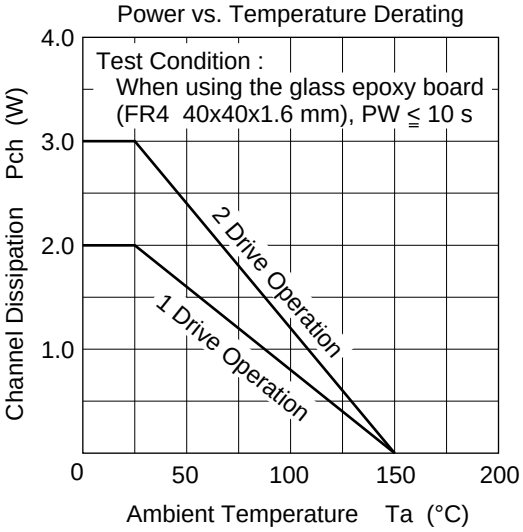
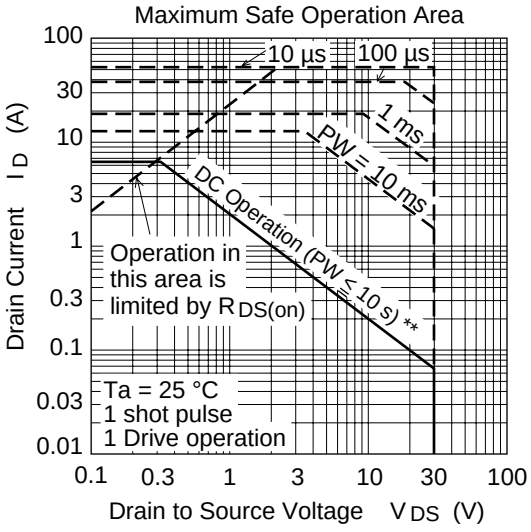
Table 2 Electrical Characteristics (Ta = 25°C)

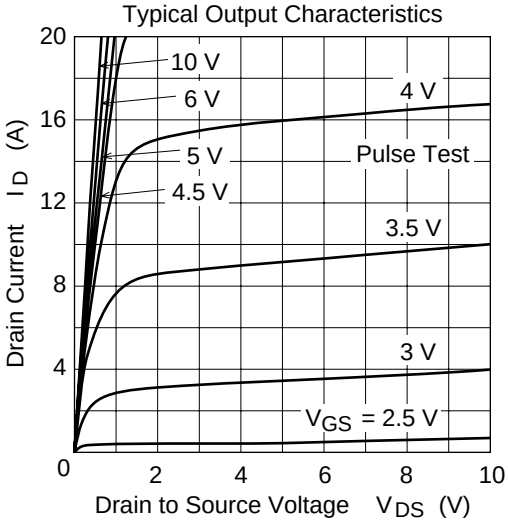
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	30	—	—	V	I_D = 10 mA, V_{GS} = 0
Gate to source breakdown voltage	$V_{(BR)GSS}$	±20	—	—	V	I_G = ±100 µA, V_{DS} = 0
Gate to source leak current	I_{GSS}	—	—	±10	µA	V_{GS} = ±16 V, V_{DS} = 0
Zero gate voltage drain current	I_{DSS}	—	—	10	µA	V_{DS} = 30 V, V_{GS} = 0
Gate to source cutoff voltage	$V_{GS(off)}$	1.0	—	2.0	V	V_{DS} = 10 V, I_D = 1 mA
Static drain to source on state resistance	$R_{DS(on)}$	—	0.03	0.045	Ω	I_D = 4A V_{GS} = 10V *
		—	0.05	0.08	Ω	I_D = 4A V_{GS} = 4V *
Forward transfer admittance	$\|y_{fs}\|$	5	8	—	S	I_D = 4 A V_{DS} = 10 V *
Input capacitance	Ciss	—	560	—	pF	V_{DS} = 10 V
Output capacitance	Coss	—	380	—	pF	V_{GS} = 0
Reverse transfer capacitance	Crss	—	170	—	pF	f = 1 MHz
Turn–on delay time	$t_{d(on)}$	—	30	—	ns	V_{GS} = 4 V, I_D = 4 A
Rise time	t_r	—	270	—	ns	V_{DD} = 10 V
Turn–off delay time	$t_{d(off)}$	—	40	—	ns	
Fall time	t_f	—	65	—	ns	
Body–drain diode forward voltage	V_{DF}	—	0.9	—	V	I_F = 6.5A, V_{GS} = 0
Body–drain diode reverse recovery time	t_{rr}	—	45	—	ns	I_F = 6.5A, V_{GS} = 0 diF / dt = 20 A / µs

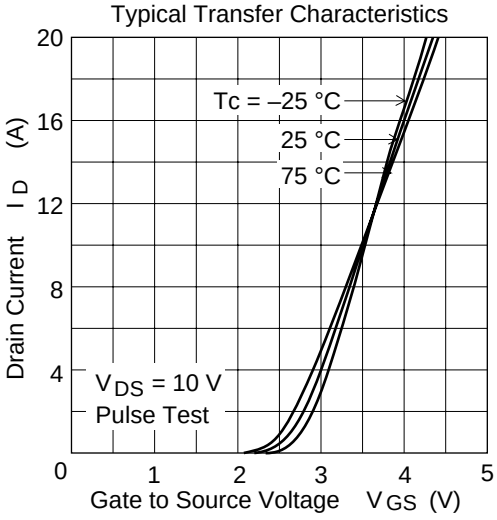
* Pulse Test





** When using the glass epoxy board
(FR4 40 x 40x 1.6 mm)





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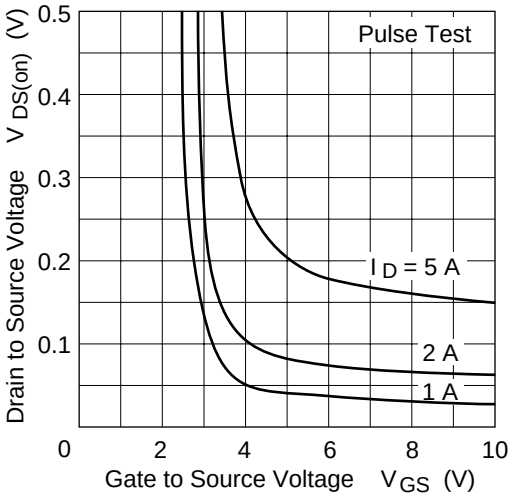
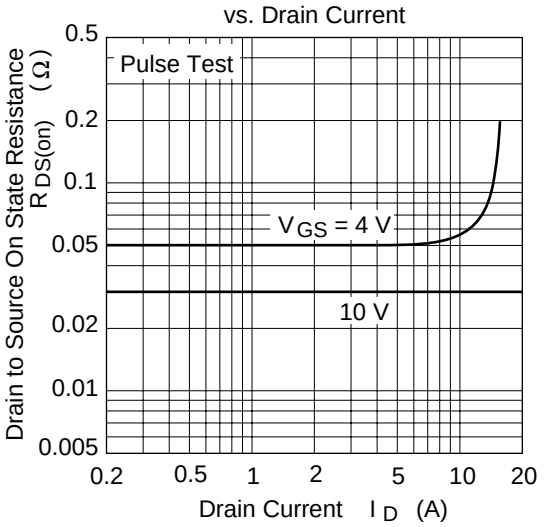
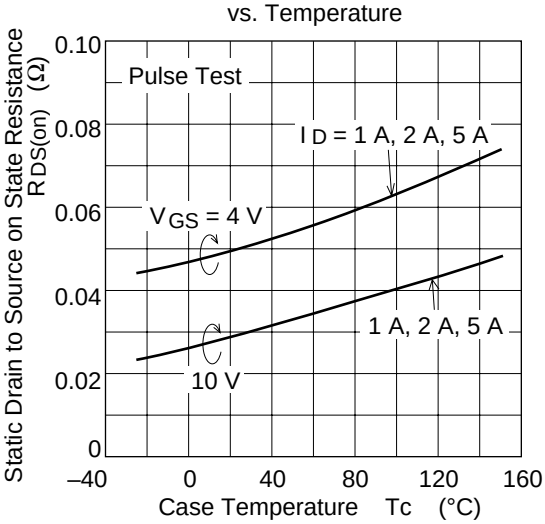
Drain to Source Saturation Voltage vs. Gate to Source Voltage



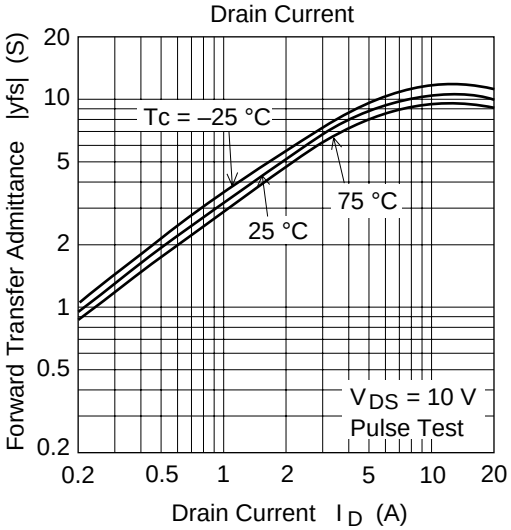
Static Drain to Source on State Resistance vs. Drain Current



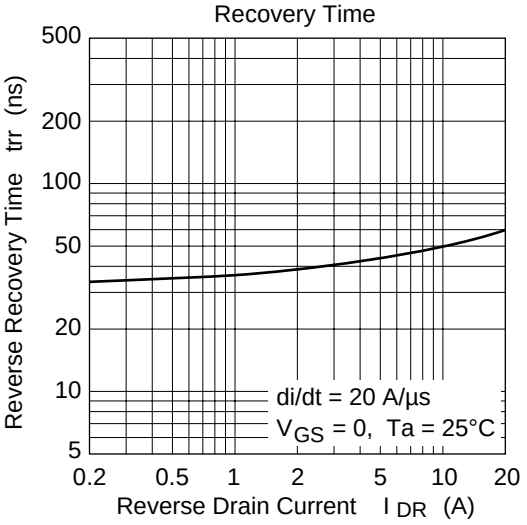
Static Drain to Source on State Resistance vs. Temperature



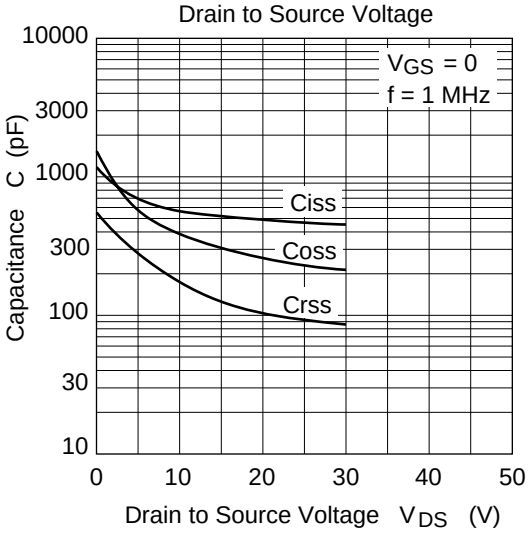
Forward Transfer Admittance vs. Drain Current



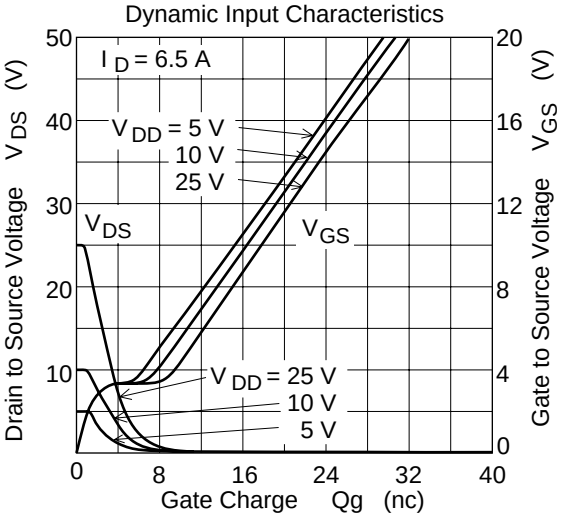
Body–Drain Diode Reverse Recovery Time



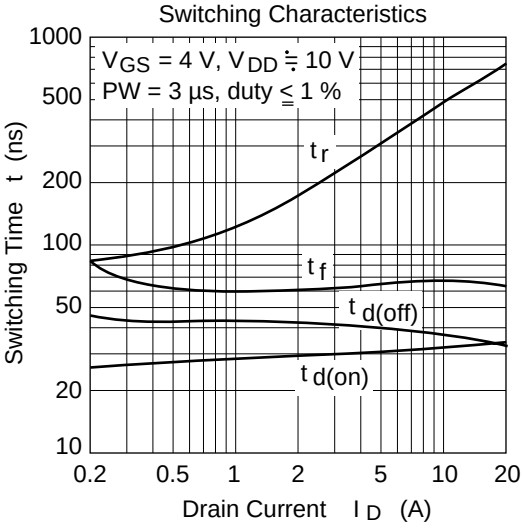
Typical Capacitance vs. Drain to Source Voltage



Dynamic Input Characteristics



Switching Characteristics



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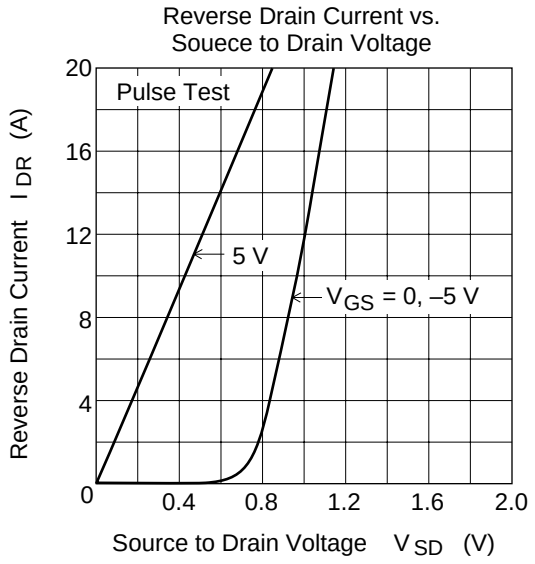
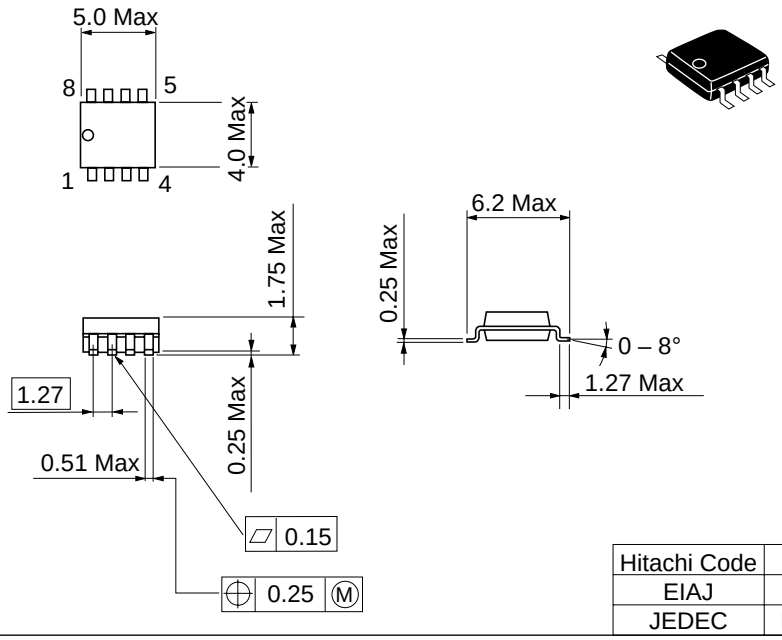


Package Dimensions

Unit : mm

• SOP–8



Hitachi Code	FP–8DA
EIAJ	—
JEDEC	MS-012AA